US 20240244845A1

(19) **United States**

(12) **Patent Application Publication** (10) **Pub. No.: US 2024/0244845 A1**

Liu et al. (43) **Pub. Date: Jul. 18, 2024**

(54) **ELECTRONIC DEVICES COMPRISING REDUCED CHARGE CONFINEMENT REGIONS IN STORAGE NODES OF PILLARS AND RELATED METHODS AND SYSTEMS**

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(21) Appl. No.: **18/622,671**

(22) Filed: **Mar. 29, 2024**

Related U.S. Application Data

(62) Division of application No. 17/092,916, filed on Nov. 9, 2020, now Pat. No. 11,956,954.

Publication Classification

(51) **Int. Cl.**

H10B 43/27	(2006.01)
H01L 23/522	(2006.01)
H10B 43/10	(2006.01)
H10B 43/35	(2006.01)
H10B 43/40	(2006.01)

(52) **U.S. Cl.**

CPC ***H10B 43/27*** (2023.02); ***H01L 23/5226*** (2013.01); ***H10B 43/10*** (2023.02); ***H10B 43/35*** (2023.02); ***H10B 43/40*** (2023.02)

(57) **ABSTRACT**

An electronic device comprises a stack of alternating dielectric materials and conductive materials, a pillar region extending vertically through the stack, an oxide material within the pillar region and laterally adjacent to the dielectric materials and the conductive materials of the stack, and a storage node laterally adjacent to the oxide material and within the pillar region. A charge confinement region of the storage node is in horizontal alignment with the conductive materials of the stack. A height of the charge confinement region in a vertical direction is less than a height of a respective, laterally adjacent conductive material of the stack in the vertical direction. Related methods and systems are also disclosed.